



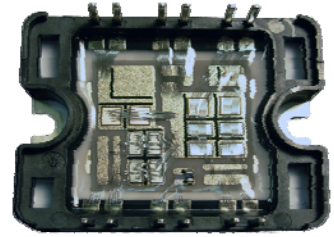
SemiSouth – światowy lider w dziedzinie półprzewodników mocy z węgla krzemu.

- 1200 V – 1700 V Trench “normally – off” JFETs
- 1200 V Trench “normally – on” JFETs
- 1200 V Schottky Diodes

Elementy półprzewodnikowe SiC firmy SemiSouth biją wszelkie rekordy pod względem sprawności, uzyskiwanych gęstości mocy oraz niezawodności.



Gate Drivers



High Power Modules

SiC Schottky Barrier Diodes

- 1200 V
- Od 5 A do 60 A

SiC Vertical Junction Field Effect Transistor

- 1200 V oraz 1700 V
- Rds(on) od 45 mΩ do 550 mΩ

TO-247-3L



TO-220-3L



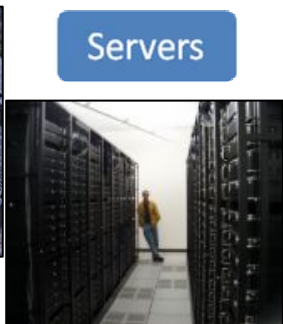
TO-220-2L



DPAK



Solar



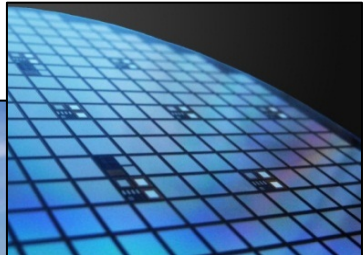
Servers



HEV



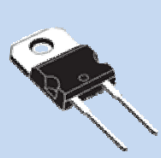

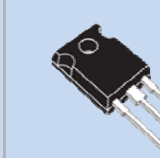
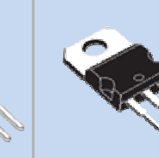
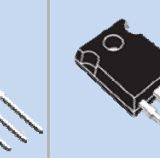
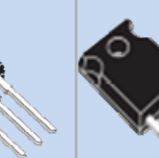
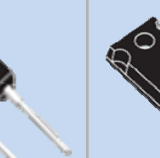
Wind



SiC Wafer



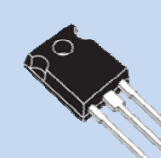
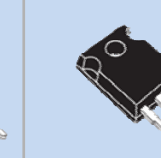
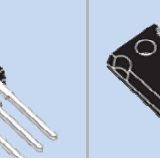
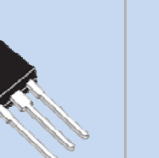

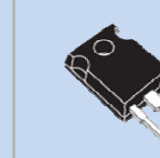
2008-11 SBD Products

Part	SDA05S120	SDB05S120	SDP10S120D	SDA10S120	SDP20S120D	SDP30S120	SDP60S120D
Package	 2L TO-220	 DPAK 2L (TO-252)	 3L TO-247	 2L TO-220	 3L TO-247	 2L TO-247	 3L TO-247
BV (V)	1200	1200	1200	1200	1200	1200	1200
I_F (A)	5A	5A	10A (2 x 5A)	10A	20A (2 x 10A)	30A	60A (2 x 30A)
Samples	2008	Now	2008	2008	2008	2009	Now
Production	2008	EQ2/2011	2008	2008	2008	2009	EQ3/2011

2008-11 Vertical JFET Products

Normally-ON

Normally-OFF

Part	SJDP120R085	SJDP120R045	SJEP120R100	SJEP120R063	SJEC120R050	SJEP170R550
Package	 3L TO-247	 3L TO-247	 3L TO-247	 3L TO-247	 Bare Die Only	 3L TO-247
Voltage	1200 V	1200 V	1200 V	1200 V	1200 V	1700V
R_{ds(on)}	85 mΩ	45 mΩ	100 mΩ	63 mΩ	50 mΩ	550 mΩ
Samples	2009	2011	2008	2009	2010	2009
Production	2009	Q3/2011	2008	2009	Q2/2011	2009